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# Vishay Siliconix

# N-Channel 100 V (D-S) MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	100				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.057				
Q <sub>g</sub> typ. (nC)	8.4				
I <sub>D</sub> (A)	15.1 <sup>a</sup>				
Configuration	Single				

#### **FEATURES**

- $\bullet$  ThunderFET technology optimizes balance of  $R_{DS(\text{on})},\,Q_g,\,Q_{sw}$  and  $Q_{oss}$
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

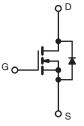


RoHS COMPLIANT

HALOGEN FREE

#### **APPLICATIONS**

- Fixed telecom
- DC/DC converter
- Primary and secondary side switch
- LED lighting



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	Si7322ADN-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	100	V	
Gate-source voltage		$V_{GS}$	± 20	† V	
	T <sub>C</sub> = 25 °C		15.1 <sup>a</sup>		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C		12.1	Ī	
	T <sub>A</sub> = 25 °C	I <sub>D</sub>	5.4 <sup>b, c</sup>	Í	
	T <sub>A</sub> = 70 °C		4.3 b, c	1	
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	20	Α	
Continuous source-drain diode current	T <sub>C</sub> = 25 °C		21.7		
	T <sub>A</sub> = 25 °C	l <sub>S</sub>	2.7 b, c		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	6	Ī	
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	1.8	mJ	
	T <sub>C</sub> = 25 °C		26		
Maximum navvay discination	T <sub>C</sub> = 70 °C		16.7	W	
Maximum power dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.3 b, c		
	T <sub>A</sub> = 70 °C	1	2.1 <sup>b, c</sup>		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature) c		, and the second	260	1	

THERMAL RESISTANCE RATING	S				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	t ≤ 10 s	R <sub>thJA</sub>	31	38	°C/W
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	4	4.8	C/VV

## Notes

- a.  $T_C = 25$  °C
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 :
- 6. 1 10 3 See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 81 °C/W



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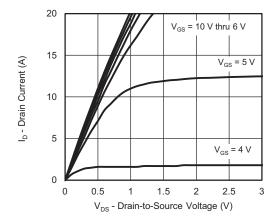
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	. OFO A	-	55	-	) //0.6
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250  \mu A$	-	-6	-	mV/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	-	4	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
Zava gata valtaga duain avuunt	,	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	-	-	10	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10	-	-	Α
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> =10 V, I <sub>D</sub> = 5.5 A	-	0.045	0.057	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 5.5 A	-	12	-	S
Dynamic <sup>b</sup>				•	•	
Input capacitance	C <sub>iss</sub>		-	360	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	130	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	18	-	1
Total gate charge	$Q_g$		-	8.4	13	
Gate-source charge	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	-	1.7	-	nC
Gate-drain charge	Q <sub>gd</sub>		-	2.6	-	
Gate resistance	$R_g$	f = 1 MHz	0.56	2.8	5.6	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	6	15	
Rise time	t <sub>r</sub>	$f = 1 \text{ MHz}$ $V_{DD} = 50 \text{ V}, \text{ R}_{L} = 10 \Omega, \text{ I}_{D} \cong 5 \text{ A},$ $V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		18	40	1
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	9	20	ns
Fall time	t <sub>f</sub>		-	13	25	
<b>Drain-Source Body Diode Characteristi</b>	cs			•	•	
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	21.7	^
Pulse diode forward current	I <sub>SM</sub>		-	-	20	A
Body diode voltage	$V_{SD}$	$I_{S} = 5 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.85	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>		-	32	60	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	L 5 A 41/44 400 A /v- T 05 00	-	32	60	nC
Reverse recovery fall time	t <sub>a</sub>	$I_F = 5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 °\text{C}$	-	23	-	
Reverse recovery rise time	t <sub>b</sub>		_	9	-	ns

#### Notes

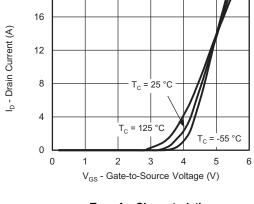
- a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



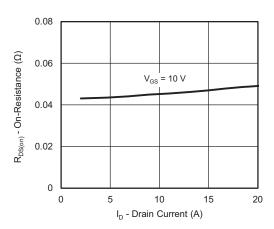


#### **Output Characteristics**

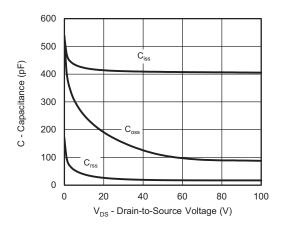


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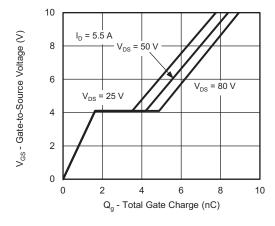
**Transfer Characteristics** 



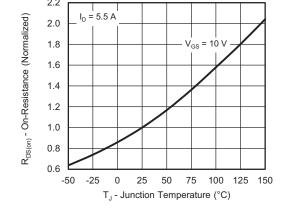
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

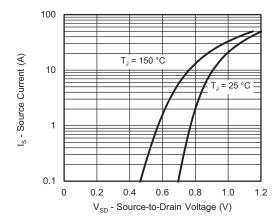


**Gate Charge** 

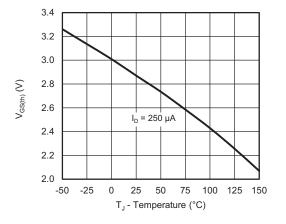


On-Resistance vs. Junction Temperature

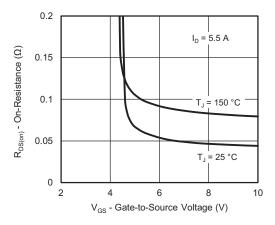




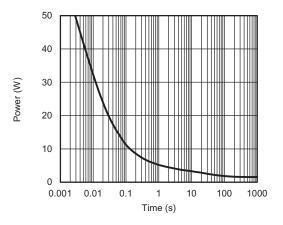
Source-Drain Diode Forward Voltage



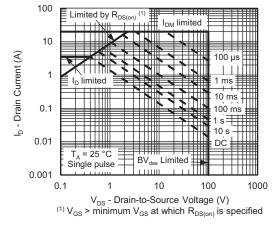
**Threshold Voltage** 



On-Resistance vs. Gate-to-Source Voltage

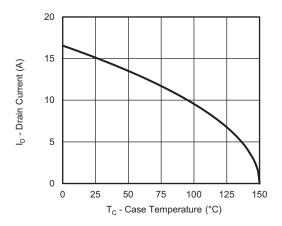


Single Pulse Power, Junction-to-Ambient

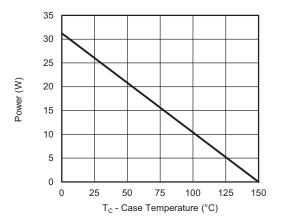


Safe Operating Area, Junction-to-Ambient





Current Derating a

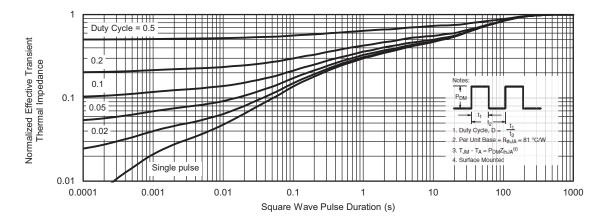


Power, Junction-to-Case

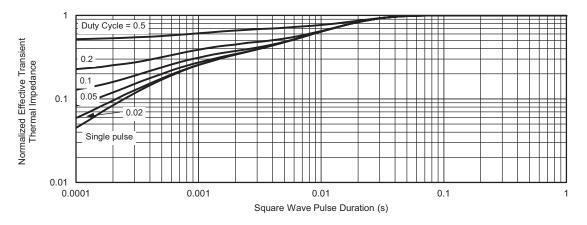
#### Note

a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





#### Normalized Thermal Transient Impedance, Junction-to-Ambient

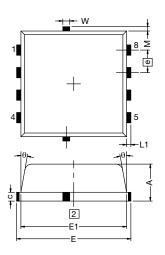


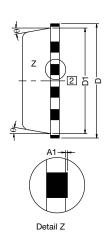
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?75590">www.vishay.com/ppg?75590</a>.



# PowerPAK® 1212-8, (Single / Dual)

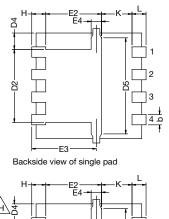


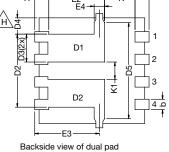


#### Notes

DWG: 5882

- 1. Inch will govern
- Dimensions exclusive of mold gate burrs
   Dimensions exclusive of mold flash and cutting burrs



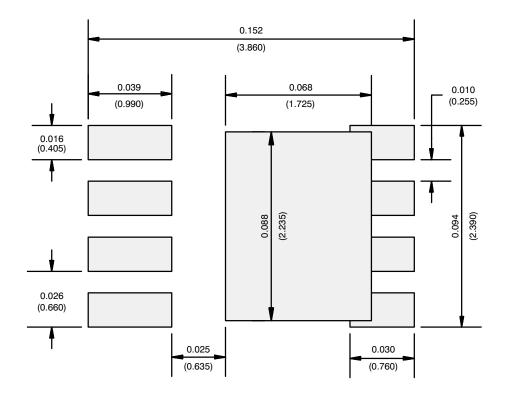


DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0.00	=	0.05	0.000	-	0.002	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D3	0.48	-	0.89	0.019	-	0.035	
D4	0.47 typ.			0.0185 typ			
D5	2.3 typ.			0.090 typ			
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.034 typ.		0.013 typ.			
е		0.65 BSC		0.026 BSC			
K		0.86 typ.		0.034 typ.			
K1	0.35	-	-	0.014	-	-	
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			

Revison: 09-Jan-17 Document Number: 71656



# RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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